

**Amendments to the Claims:**

This listing of claims will replace all prior versions, and listings, of claims in the application:

**Listing of Claims:**

Claims 1 – 54 (canceled)

55. (currently amended) A chip package comprising:

a substrate having a first side and a second side opposite to said first side, wherein said substrate comprises multiple contact points at said second side, a solder mask at said first side, an interconnect covered by said solder mask and a first metal pad comprising a region uncovered ~~exposed by an opening in said solder mask, wherein said~~ first metal pad is connected to said interconnect;

a chip over said first side of said substrate, wherein said chip comprises a silicon substrate, multiple layers of interconnecting lines comprising copper, multiple insulating layers comprising an oxide material, multiple metal vias in said multiple insulating layers and between said multiple layers of interconnecting lines, wherein said multiple metal vias are connected to said multiple layers of interconnecting lines, and a polymer layer, ~~wherein an opening in said polymer layer exposes a second metal pad of said multiple layers of interconnecting lines;~~

a copper pillar between said first metal pad and a second metal pad of said multiple layers of interconnecting lines, pads, wherein said copper pillar is connected to

said second metal pad through said ~~an~~ opening in said polymer layer, and wherein said copper pillar has a thickness between 10 and 100 micrometers;

a titanium-containing layer between said second metal pad and said copper pillar, wherein said titanium-containing layer is on said second metal pad, on said polymer layer and in said opening in said polymer layer;

a solder metal between said copper pillar and said first metal pad, wherein said solder metal is connected to said first metal pad;

a nickel-containing layer between said copper pillar and said solder metal; and

an underfill between said chip and said first side of said substrate, wherein said underfill contacts with said chip and said first side of said substrate and encloses said copper pillar.

Claim 56 (canceled)

57. (currently amended) The chip package of Claim 55, wherein said substrate further comprises multiple third metal pads ~~exposed by said opening in~~ uncovered by said solder mask, wherein said solder mask is separate from said first metal pad and from said multiple third metal pads, and wherein said first metal pad and said multiple third metal pads are aligned in a direction parallel with a sidewall of ~~said opening in said solder mask,~~ wherein said first metal pad is connected to said interconnect through said sidewall.

58. (currently amended) The chip package of Claim 55, ~~wherein said copper pillar has a transverse dimension smaller than that of said nickel-containing layer, wherein said copper pillar has a first sidewall recessed from a second sidewall of said nickel-containing layer, wherein a distance between said first sidewall and said second sidewall is greater than 0.2 micrometers, and wherein said nickel-containing layer comprises a first portion over said copper pillar and a second portion overhanging said copper pillar.~~

Claim 59 (canceled)

60. (previously presented) The chip package of Claim 55, wherein said substrate comprises a ball grid array substrate.

61. (previously presented) The chip package of Claim 55, where said multiple contact points comprise multiple contact balls at said second side.

62. (previously presented) The chip package of Claim 55, wherein said first metal pad has a circular shape.

Claims 63-65 (canceled)

66. (previously presented) The chip package of Claim 55, wherein said nickel-containing layer has a thickness between 1 and 10 micrometers.

67. (previously presented) The chip package of Claim 55, wherein said titanium-containing layer comprises titanium nitride.

68. (previously presented) The chip package of Claim 55, wherein said copper pillar is electroplated.

69. (currently amended) A chip package comprising:

a substrate having a first side and a second side opposite to said first side, wherein said substrate comprises multiple contact points at said second side, a solder mask at said first side, an interconnect covered by said solder mask and a first metal pad comprising a region uncovered exposed by an opening in said solder mask, wherein said first metal pad is connected to said interconnect;

a chip over said first side of said substrate, wherein said chip comprises a silicon substrate, multiple layers of interconnecting lines comprising copper, multiple insulating layers comprising an oxide material, multiple metal vias in said multiple insulating layers and between said multiple layers of interconnecting lines, wherein said multiple metal vias are connected to said multiple layers of interconnecting lines, and a polymer layer; wherein an opening in said polymer layer exposes a second metal pad of said multiple layers of interconnecting lines;

a copper pillar between said first metal pad and a second metal pad of said multiple layers of interconnecting lines, pads, wherein said copper pillar is connected to

said second metal pad through said ~~an~~ opening in said polymer layer, and wherein said copper pillar has a thickness between 10 and 100 micrometers;

a ~~barrier-metal~~ layer between said second metal pad and said copper pillar, wherein said ~~barrier-metal~~ layer is on said second metal pad, on said polymer layer and in said opening in said polymer layer;

a solder metal between said copper pillar and said first metal pad, wherein said solder metal is connected to said first metal pad; and

~~a nickel-containing layer between said copper pillar and said solder metal; and~~

an underfill between said chip and said first side of said substrate, wherein said underfill contacts with said chip and said first side of said substrate and encloses said copper pillar.

70. (currently amended) The chip package of Claim 69, wherein said substrate further comprises multiple third metal pads uncovered by ~~exposed by said opening in said solder mask, wherein said solder mask is separate from said first metal pad and from said multiple third metal pads, and wherein said first metal pad and said multiple third metal pads are aligned in a direction parallel with a sidewall of said opening in said solder mask, wherein said first metal pad is connected to said interconnect through said~~ sidewall.

71. (currently amended) The chip package of Claim 69 further comprising a nickel-containing layer between said copper pillar and said solder metal. ~~, wherein said copper pillar has a transverse dimension smaller than that of said nickel-containing layer,~~

~~wherein said copper pillar has a first sidewall recessed from a second sidewall of said nickel-containing layer, wherein a distance between said first sidewall and said second sidewall is greater than 0.2 micrometers, and wherein said nickel-containing layer comprises a first portion over said copper pillar and a second portion overhanging said copper pillar.~~

72. (previously presented) The chip package of Claim 69, wherein said substrate comprises a ball grid array substrate.

73. (previously presented) The chip package of Claim 69, where said multiple contact points comprise multiple contact balls at said second side.

74. (previously presented) The chip package of Claim 69, wherein said first metal pad has a circular shape.

75. (currently amended) The chip package of Claim 71, ~~69~~, wherein said nickel-containing layer has a thickness between 1 and 10 micrometers.

76. (previously presented) The chip package of Claim 69, wherein said copper pillar is electroplated.

77. (new) The chip package of Claim 69, wherein said metal layer comprises titanium.

78. (new) The chip package of Claim 69, wherein said metal layer comprises a titanium nitride.

79. (new) The chip package of Claim 69, wherein said metal layer comprises tungsten.

80. (new) The chip package of Claim 69, wherein said metal layer comprises tantalum.